

### 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



### DISCRETE SEMICONDUCTORS

## DATA SHEET

# BT258 series Thyristors logic level

**Product specification** 

October 2002



### Thyristors logic level

BT258 series

### **GENERAL DESCRIPTION**

# Passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

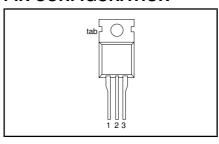
### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V <sub>DRM</sub> , V <sub>RRM</sub> I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	BT258- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state	<b>500R</b> 500 5 8 75	600R 600 5 8 75	800R 800 5 8 75	V A A A

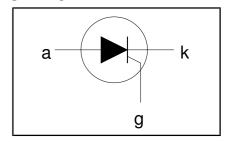
### **PINNING - TO220AB**

PIN	DESCRIPTION	
1	cathode	
2	2 anode	
3	gate	
tab	anode	

### **PIN CONFIGURATION**



### **SYMBOL**



### **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
V <sub>DRM</sub> , V <sub>RRM</sub>	Repetitive peak off-state voltages		-	<b>-500R</b> 500 <sup>1</sup>	<b>-600R</b> 600 <sup>1</sup>	<b>-800R</b> 800	V
I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 111  ^{\circ}\text{C}$ all conduction angles half sine wave; $T_{j} = 25  ^{\circ}\text{C}$ prior to surge	-		5 8		A A
l²t dl <sub>⊤</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after triggering	t = 10  ms t = 8.3  ms t = 10  ms $l_{TM} = 10 \text{ A}; l_G = 50 \text{ mA};$ $dl_G/dt = 50 \text{ mA}/\mu s$	- - -		75 82 28 50		A A A²s A/μs
I <sub>GM</sub> V <sub>RGM</sub> P <sub>GM</sub> P <sub>G(AV)</sub> T <sub>stg</sub> T <sub>j</sub>	Peak gate current Peak reverse gate voltage Peak gate power Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- - - -40 -		2 5 5 0.5 150 125 <sup>2</sup>		۵°,0°

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu$ s.

**<sup>2</sup>** Note: Operation above 110°C may require the use of a gate to cathode resistor of  $1k\Omega$  or less.

Thyristors logic level

BT258 series

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	Thermal resistance		-	-	2.0	K/W
R <sub>th j-a</sub>	junction to mounting base Thermal resistance junction to ambient	in free air	-	60	-	K/W

### STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	50	200	μA
I <sub>L</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	0.4	10	mΑ
I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	0.3	6	mA
ĺΫ́	On-state voltage	$I_{T} = 16 \text{ A}$	-	1.3	1.6	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.4	1.5	V
		$V_D = V_{DRM(max)}$ ; $I_T = 0.1 A$ ; $T_j = 110 °C$	0.1	0.2	-	V
$I_D, I_R$	Off-state leakage current	$V_D = V_{DRM(max)}^{DRM(max)}; V_R = V_{RRM(max)}; T_j = 125 °C$	-	0.1	0.5	mA

### **DYNAMIC CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	$V_{DM}$ = 67% $V_{DRM(max)}$ ; $T_j$ = 125 °C; exponential waveform; $R_{GK}$ = 100 Ω	50	100	1	V/μs
t <sub>gt</sub>	Gate controlled turn-on time	$I_{TM} = 10 \text{ A}; V_D = V_{DRM(max)}; \widetilde{I}_G = 5 \text{ mA};$ $dI_G/dt = 0.2 \text{ A/us}$	-	2	-	μs
t <sub>q</sub>	Circuit commutated turn-off time	$ \begin{vmatrix} V_D = 67\% \ V_{DRM(max)}; \ T_j = 125 \ ^{\circ}C; \\ I_{TM} = 12 \ A; \ V_R = 24 \ V; \ dI_{TM}/dt = 10 \ A/\mu s; \\ dV_D/dt = 2 \ V/\mu s; \ R_{GK} = 1 \ k\Omega $	-	100	-	μs

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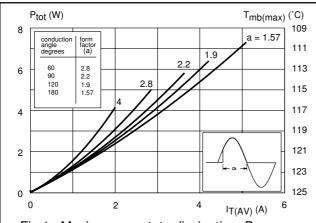


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus average on-state current,  $I_{T(AV)}$ , where  $a = form\ factor = I_{T(RMS)}/I_{T(AV)}$ .

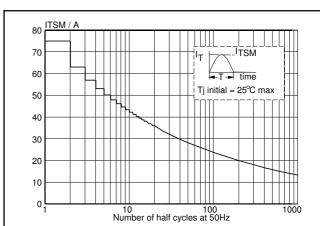


Fig.4. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

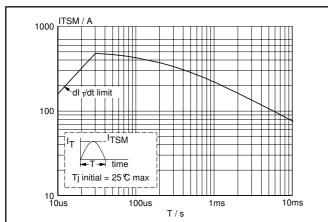


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 10$ ms.

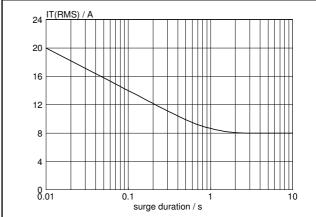


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 111$  °C.

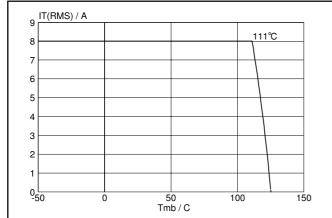
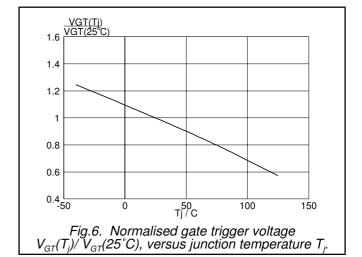
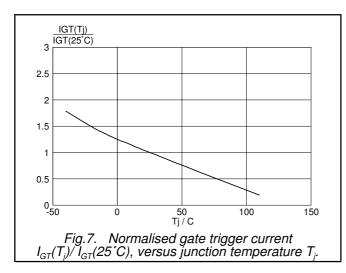


Fig.3. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .



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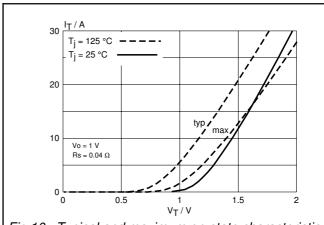
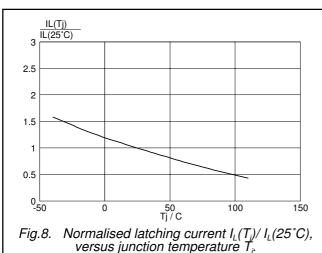
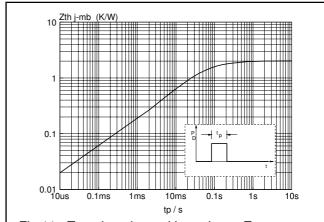


Fig.10. Typical and maximum on-state characteristic.





3

IH(Tj)

H(25°C)

2.5

2

1.5

1

0.5

0

-50

0

50

Tj/C

Fig.11. Transient thermal impedance  $Z_{th j-mb}$ , versus pulse width  $t_p$ .

Normalised holding current  $I_H(T_i)/I_H(25^{\circ}C)$ , versus junction temperature  $T_i$ .

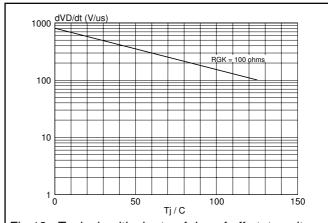
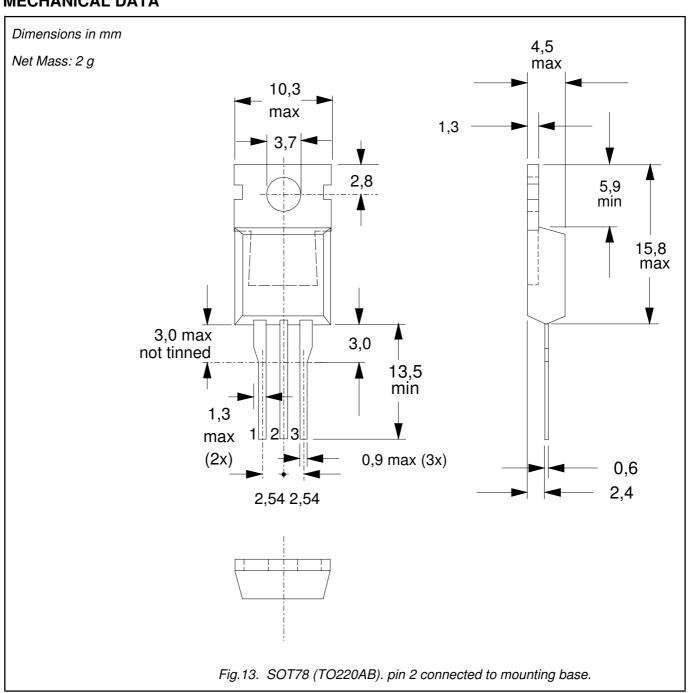


Fig. 12. Typical, critical rate of rise of off-state voltage,  $dV_D/dt$  versus junction temperature  $T_j$ .

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### **MECHANICAL DATA**



- Notes
  1. Refer to mounting instructions for SOT78 (TO220) envelopes.
  2. Epoxy meets UL94 V0 at 1/8".

### Legal information

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION	
Objective data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.	
Product data sheet Production This document contains the product specification.		This document contains the product specification.	

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